

CMXT3906

**SURFACE MOUNT
DUAL PNP
SILICON TRANSISTORS**



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMXT3906 type is a dual PNP silicon transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, and designed for small signal general purpose amplifier and switching applications.



SOT-26 CASE

MARKING CODE: X2A

MAXIMUM RATINGS: ($T_A=25^{\circ}\text{C}$)

| |
|--|
| Collector-Base Voltage |
| Collector-Emitter Voltage |
| Emitter-Base Voltage |
| Continuous Collector Current |
| Power Dissipation |
| Operating and Storage Junction Temperature |
| Thermal Resistance |

SYMBOL

| | |
|----------------|-------------|
| V_{CBO} | 40 |
| V_{CEO} | 40 |
| V_{EBO} | 5.0 |
| I_C | 200 |
| P_D | 350 |
| T_J, T_{stg} | -65 to +150 |
| θ_{JA} | 357 |

UNITS

| |
|-----------------------------|
| V |
| V |
| V |
| mA |
| mW |
| $^{\circ}\text{C}$ |
| $^{\circ}\text{C}/\text{W}$ |

ELECTRICAL CHARACTERISTICS PER TRANSISTOR: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

| SYMBOL | TEST CONDITIONS | MIN | MAX | UNITS |
|---------------|--|------|------|------------|
| I_{CEV} | $V_{CE}=30\text{V}, V_{EB}=3.0\text{V}$ | | 50 | nA |
| BV_{CBO} | $I_C=10\mu\text{A}$ | 40 | | V |
| BV_{CEO} | $I_C=1.0\text{mA}$ | 40 | | V |
| BV_{EBO} | $I_E=10\mu\text{A}$ | 5.0 | | V |
| $V_{CE(SAT)}$ | $I_C=10\text{mA}, I_B=1.0\text{mA}$ | | 0.25 | V |
| $V_{CE(SAT)}$ | $I_C=50\text{mA}, I_B=5.0\text{mA}$ | | 0.40 | V |
| $V_{BE(SAT)}$ | $I_C=10\text{mA}, I_B=1.0\text{mA}$ | 0.65 | 0.85 | V |
| $V_{BE(SAT)}$ | $I_C=50\text{mA}, I_B=5.0\text{mA}$ | | 0.95 | V |
| h_{FE} | $V_{CE}=1.0\text{V}, I_C=0.1\text{mA}$ | 60 | | |
| h_{FE} | $V_{CE}=1.0\text{V}, I_C=1.0\text{mA}$ | 80 | | |
| h_{FE} | $V_{CE}=1.0\text{V}, I_C=10\text{mA}$ | 100 | 300 | |
| h_{FE} | $V_{CE}=1.0\text{V}, I_C=50\text{mA}$ | 60 | | |
| h_{FE} | $V_{CE}=1.0\text{V}, I_C=100\text{mA}$ | 30 | | |
| f_T | $V_{CE}=20\text{V}, I_C=10\text{mA}, f=100\text{MHz}$ | 250 | | MHz |
| C_{ob} | $V_{CB}=5.0\text{V}, I_E=0, f=1.0\text{MHz}$ | | 4.5 | pF |
| C_{ib} | $V_{BE}=0.5\text{V}, I_C=0, f=1.0\text{MHz}$ | | 12 | pF |
| h_{ie} | $V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$ | 2.0 | 12 | k Ω |

CMXT3906

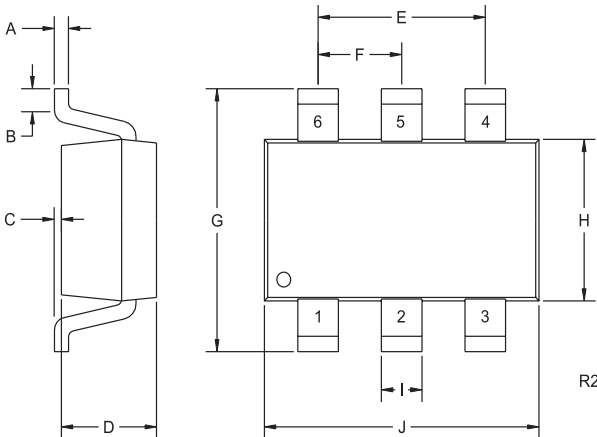
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ELECTRICAL CHARACTERISTICS PER TRANSISTOR - Continued: ($T_A=25^\circ\text{C}$ unless otherwise noted)

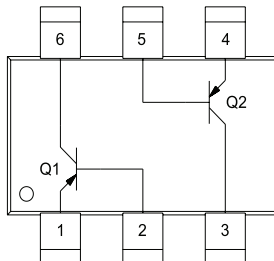
| SYMBOL | TEST CONDITIONS | MIN | MAX | UNITS |
|----------|--|-----|-----|------------------|
| h_{re} | $V_{CE}=10\text{V}$, $I_C=1.0\text{mA}$, $f=1.0\text{kHz}$ | 0.1 | 10 | $\times 10^{-4}$ |
| h_{fe} | $V_{CE}=10\text{V}$, $I_C=1.0\text{mA}$, $f=1.0\text{kHz}$ | 100 | 400 | |
| h_{oe} | $V_{CE}=10\text{V}$, $I_C=1.0\text{mA}$, $f=1.0\text{kHz}$ | 3.0 | 60 | μS |
| NF | $V_{CE}=5.0\text{V}$, $I_C=100\mu\text{A}$, $R_S=1.0\text{k}\Omega$, $f=10\text{Hz}$ to 15.7kHz | | 4.0 | dB |
| t_d | $V_{CC}=3.0\text{V}$, $V_{BE}=0.5\text{V}$, $I_C=10\text{mA}$, $I_{B1}=1.0\text{mA}$ | | 35 | ns |
| t_r | $V_{CC}=3.0\text{V}$, $V_{BE}=0.5\text{V}$, $I_C=10\text{mA}$, $I_{B1}=1.0\text{mA}$ | | 35 | ns |
| t_s | $V_{CC}=3.0\text{V}$, $I_C=10\text{mA}$, $I_{B1}=I_{B2}=1.0\text{mA}$ | | 170 | ns |
| t_f | $V_{CC}=3.0\text{V}$, $I_C=10\text{mA}$, $I_{B1}=I_{B2}=1.0\text{mA}$ | | 80 | ns |

SOT-26 CASE - MECHANICAL OUTLINE



| SYMBOL | DIMENSIONS | | | |
|--------|------------|-------|-------------|------|
| | INCHES | | MILLIMETERS | |
| | MIN | MAX | MIN | MAX |
| A | 0.004 | 0.007 | 0.11 | 0.19 |
| B | 0.016 | - | 0.40 | - |
| C | - | 0.004 | - | 0.10 |
| D | 0.039 | 0.047 | 1.00 | 1.20 |
| E | 0.074 | 0.075 | 1.88 | 1.92 |
| F | 0.037 | 0.038 | 0.93 | 0.97 |
| G | 0.102 | 0.118 | 2.60 | 3.00 |
| H | 0.059 | 0.067 | 1.50 | 1.70 |
| I | 0.016 | | 0.41 | |
| J | 0.110 | 0.118 | 2.80 | 3.00 |

SOT-26 (REV: R2)



LEAD CODE:

- 1) Emitter Q1
- 2) Base Q1
- 3) Collector Q2
- 4) Emitter Q2
- 5) Base Q2
- 6) Collector Q1

MARKING CODE: X2A

R5 (15-September 2022)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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